

PHD13005

NPN power transistor with integrated diode

Rev. 02 — 29 July 2010

Product data sheet

1. Product profile

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel E-C diode in a SOT78 plastic package.

1.2 Features and benefits

- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode
- Low thermal resistance

1.3 Applications

- Integrated fluorescent lamp ballasts e.g. high power cluster lamps
- Low Voltage Tungsten Halogen transformers
- Remote fluorescent lamp ballasts
- Self Oscillating Power Supplies

1.4 Quick reference data

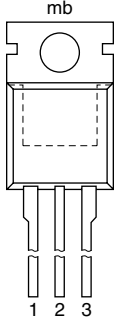
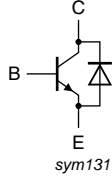
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_C	collector current	see Figure 1 ; see Figure 2 ; see Figure 4 ; DC	-	-	4	A
P_{tot}	total power dissipation	see Figure 3 ; $T_{mb} \leq 25\text{ °C}$	-	-	75	W
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	-	700	V
Static characteristics						
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; $I_C = 1.0\text{ A}$; see Figure 10	12	20	40	
		$V_{CE} = 5\text{ V}$; $I_C = 2.0\text{ A}$; see Figure 10	10	17	28	



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base		
2	C	collector		
3	E	emitter		
mb	C	mounting base; connected to collector		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHD13005	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	700	V
V_{CBO}	collector-base voltage	$I_E = 0\text{ A}$	-	700	V
V_{CEO}	collector-emitter voltage	$I_B = 0\text{ A}$	-	400	V
I_C	collector current	DC; see Figure 1 ; see Figure 2 ; see Figure 4	-	4	A
I_{CM}	peak collector current	see Figure 4 ; see Figure 1 ; see Figure 2	-	8	A
I_B	base current	DC	-	2	A
I_{BM}	peak base current		-	4	A
P_{tot}	total power dissipation	$T_{mb} \leq 25\text{ °C}$; see Figure 3	-	75	W
T_{stg}	storage temperature		-65	150	°C
T_j	junction temperature		-	150	°C

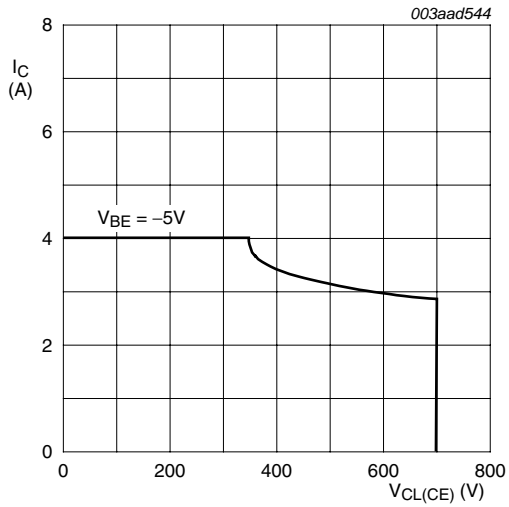
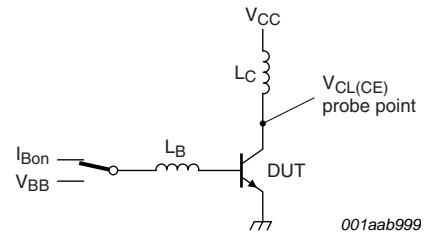
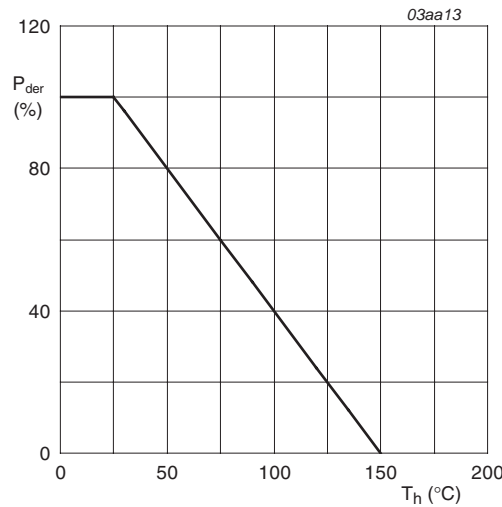


Fig 1. Reverse bias safe operating area



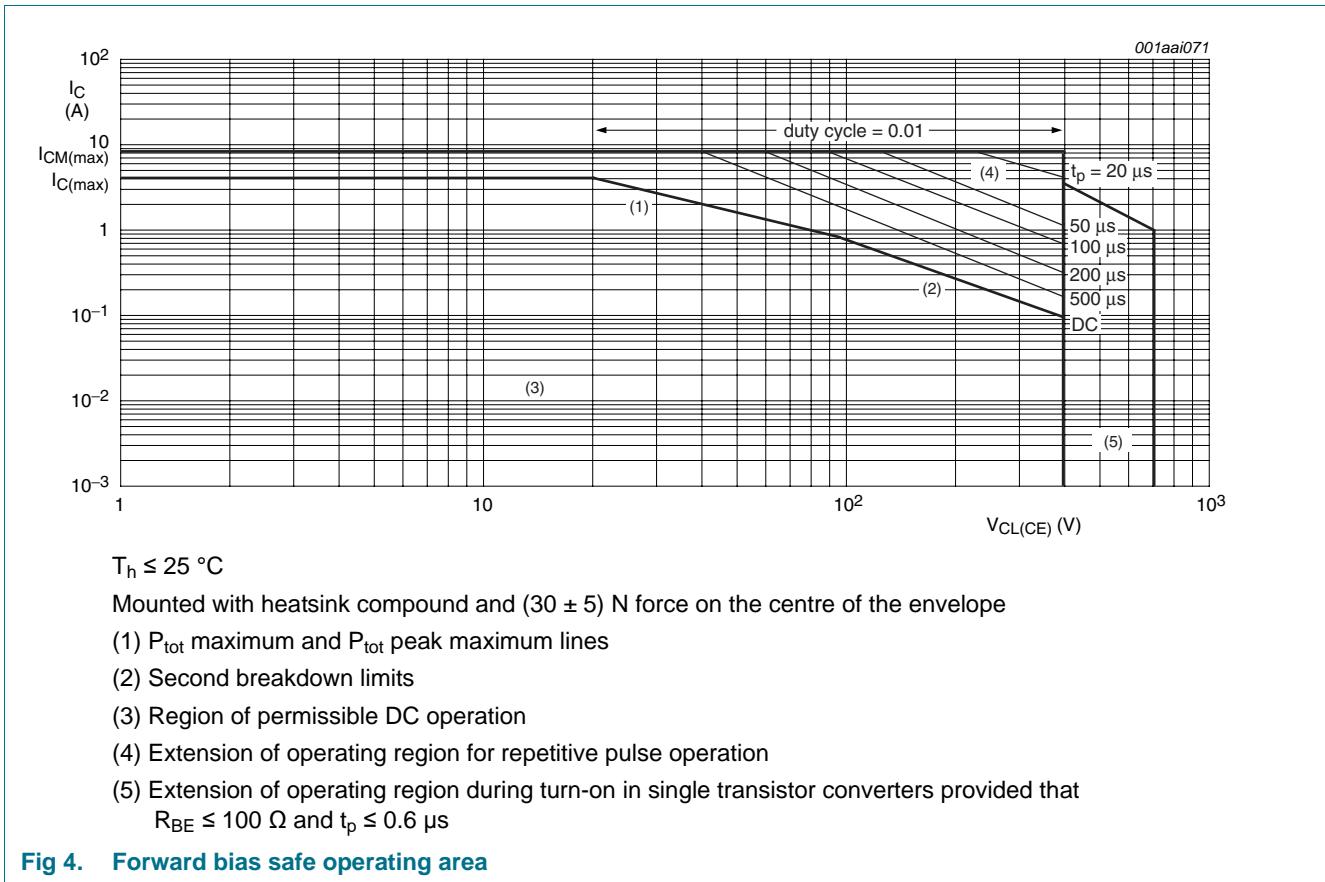
$V_{CL(CE)} \leq 1000 V; V_{CC} = 150 V; V_{BB} = -5 V;$
 $L_B = 1 \mu H; L_C = 200 \mu H$

Fig 2. Test circuit for reverse bias safe operating area



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100 \%$$

Fig 3. Normalized total power dissipation as a function of heatsink temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	1.67	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

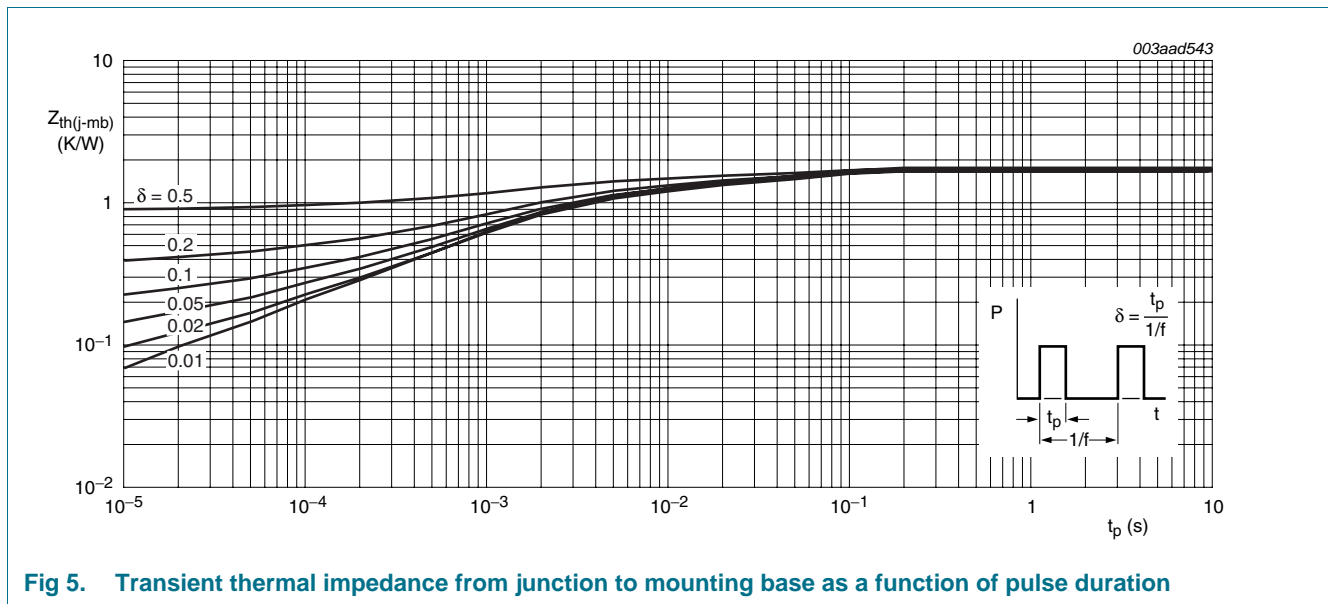


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{CES}	collector-emitter cut-off current	$V_{BE} = 0\text{ V}; V_{CE} = 700\text{ V}; T_j = 100\text{ }^\circ\text{C}$	[1]	-	5	mA
		$V_{BE} = 0\text{ V}; V_{CE} = 700\text{ V}$	[1]	-	1	mA
I_{CBO}	collector-base cut-off current	$V_{CB} = 700\text{ V}; I_E = 0\text{ A}$	[1]	-	1	mA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 400\text{ V}; I_B = 0\text{ A}$	[1]	-	0.1	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 9\text{ V}; I_C = 0\text{ A}$	-	-	10	mA
$V_{CEO_{sus}}$	collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 10\text{ mA}; L_C = 25\text{ mH};$ see Figure 6 ; see Figure 15	400	-	-	V
$V_{CE_{sat}}$	collector-emitter saturation voltage	$I_C = 1.0\text{ A}; I_B = 0.2\text{ A};$ see Figure 7 ; see Figure 8	-	0.1	0.5	V
		$I_C = 2.0\text{ A}; I_B = 0.5\text{ A};$ see Figure 7 ; see Figure 8	-	0.2	0.6	V
		$I_C = 4.0\text{ A}; I_B = 1.0\text{ A};$ see Figure 7 ; see Figure 8	-	0.3	1	V
$V_{BE_{sat}}$	base-emitter saturation voltage	$I_C = 2.0\text{ A}; I_B = 0.5\text{ A};$ see Figure 9	-	0.92	1.6	V
		$I_C = 1.0\text{ A}; I_B = 0.2\text{ A};$ see Figure 9	-	0.85	1.2	V
V_F	forward voltage	$I_F = 2.0\text{ A}$	-	1.04	1.5	V
h_{FE}	DC current gain	$I_C = 1.0\text{ A}; V_{CE} = 5\text{ V};$ see Figure 10	12	20	40	
		$I_C = 2.0\text{ A}; V_{CE} = 5\text{ V};$ see Figure 10	10	17	28	
Dynamic characteristics						
t_s	storage time	$I_C = 2.0\text{ A}; I_{B_{on}} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H};$ inductive load; see Figure 11 ; see Figure 12	-	1.2	2	μs
		$I_C = 2.0\text{ A}; I_{B_{on}} = 0.4\text{ A}; I_{B_{off}} = -0.4\text{ A};$ $R_L = 75\text{ }\Omega;$ resistive load; see Figure 13 ; see Figure 14	-	2.7	4	μs
		$I_C = 2.0\text{ A}; I_{B_{on}} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H}; T_j = 100\text{ }^\circ\text{C};$ inductive load; see Figure 11 ; see Figure 12	-	1.4	4	μs
t_f	fall time	$I_C = 2.0\text{ A}; I_{B_{on}} = 0.4\text{ A}; I_{B_{off}} = -0.4\text{ A};$ $R_L = 75\text{ }\Omega;$ resistive load; see Figure 13 ; see Figure 14	-	0.3	0.9	μs
		$I_C = 2.0\text{ A}; I_{B_{on}} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H}; T_j = 100\text{ }^\circ\text{C};$ inductive load; see Figure 11 ; see Figure 12	-	0.16	0.9	μs
		$I_C = 2.0\text{ A}; I_{B_{on}} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H};$ inductive load; see Figure 11 ; see Figure 12	-	0.1	0.5	μs

[1] measured with half-sine wave voltage (curve tracer)

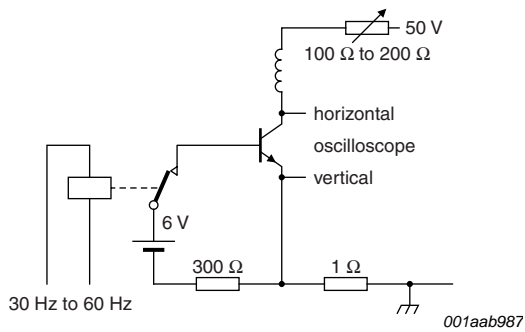
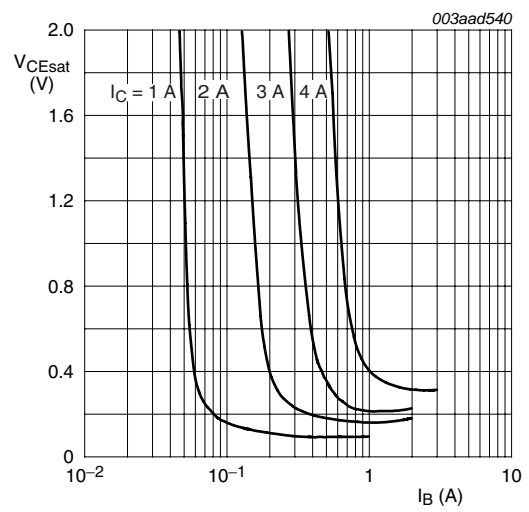
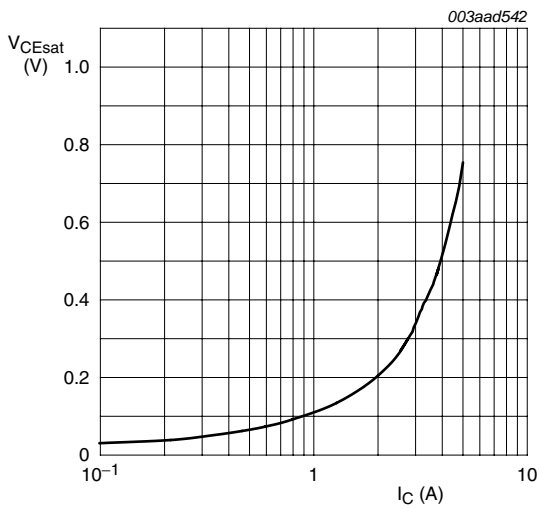


Fig 6. Test circuit for collector-emitter sustaining voltage



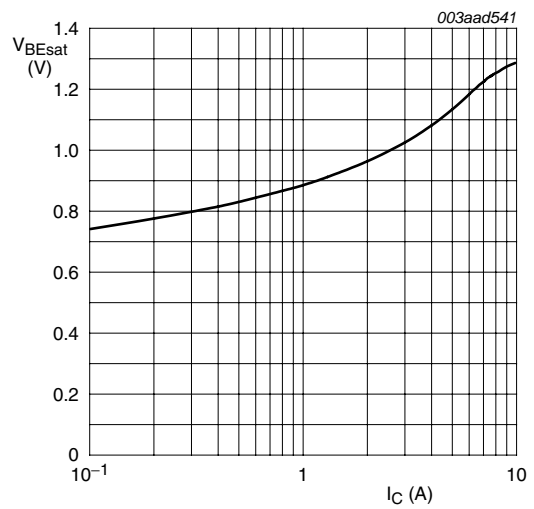
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Collector-emitter saturation voltage; typical values



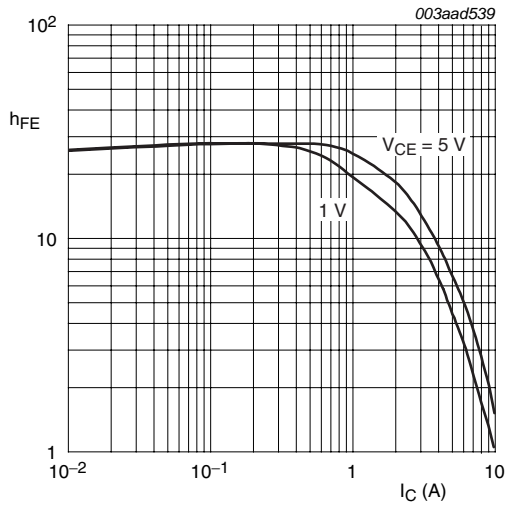
$$\frac{I_C}{I_B} = 4$$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



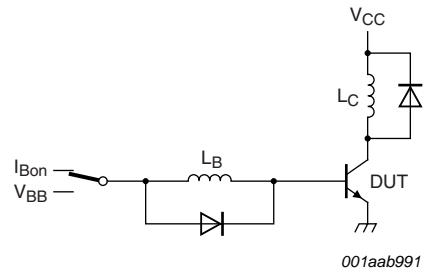
$$\frac{I_C}{I_B} = 4$$

Fig 9. Base-emitter saturation voltage; typical values



$T_j = 25\text{ }^\circ\text{C}$

Fig 10. DC current gain as a function of collector current; typical values



$V_{CC} = 300\text{ V}; V_{BB} = -5\text{ V}; L_C = 200\text{ }\mu\text{H}; L_B = 1\text{ }\mu\text{H}$

Fig 11. Test circuit for inductive load switching

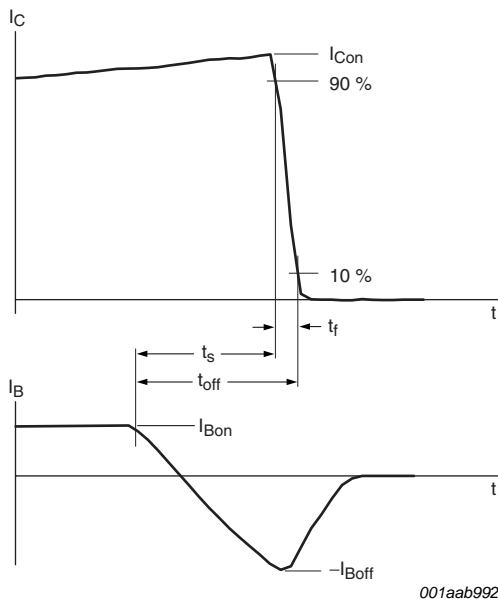
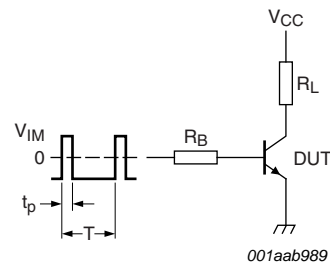


Fig 12. Switching times waveforms for inductive load



$V_{IM} = -6\text{ to }+8\text{ V}; V_{CC} = 250\text{ V}; t_p = 20\text{ }\mu\text{s}; \delta = \frac{t_p}{T} = 0.01$
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 13. Test circuit for resistive load switching

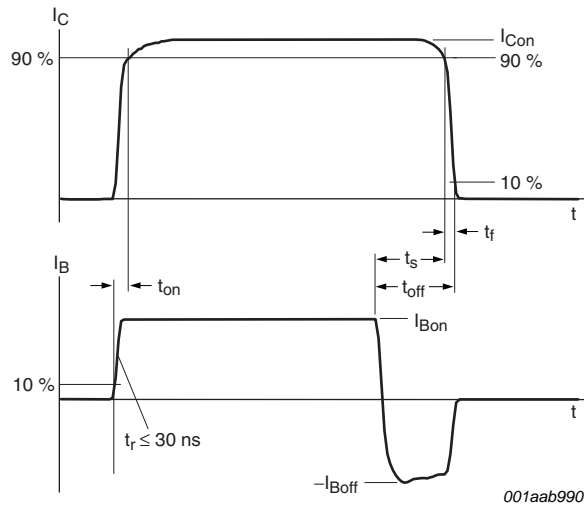


Fig 14. Switching times waveforms for resistive load

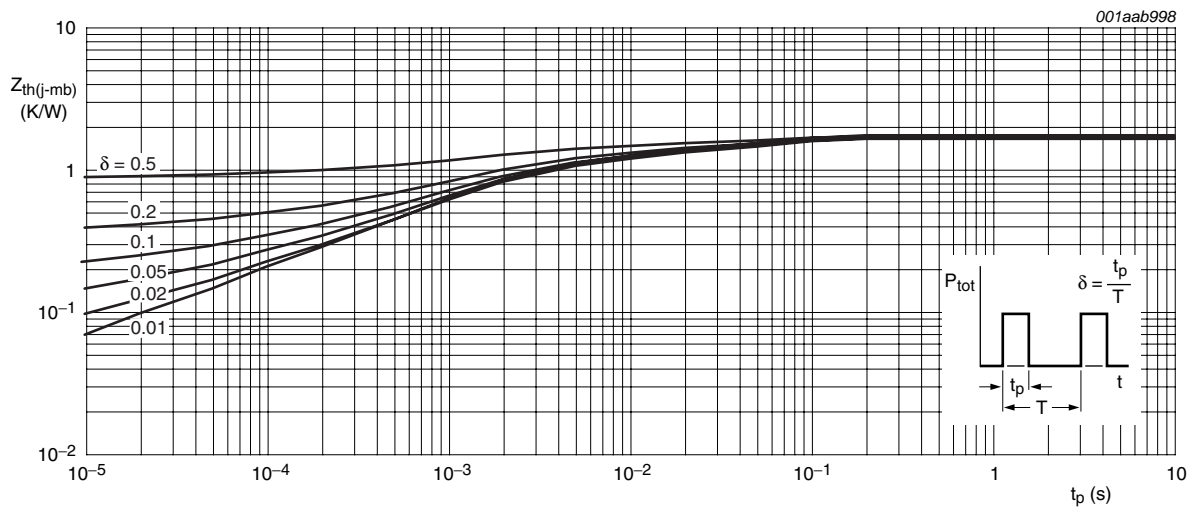


Fig 15. Transient thermal impedance from junction to mounting base as a function of pulse width

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

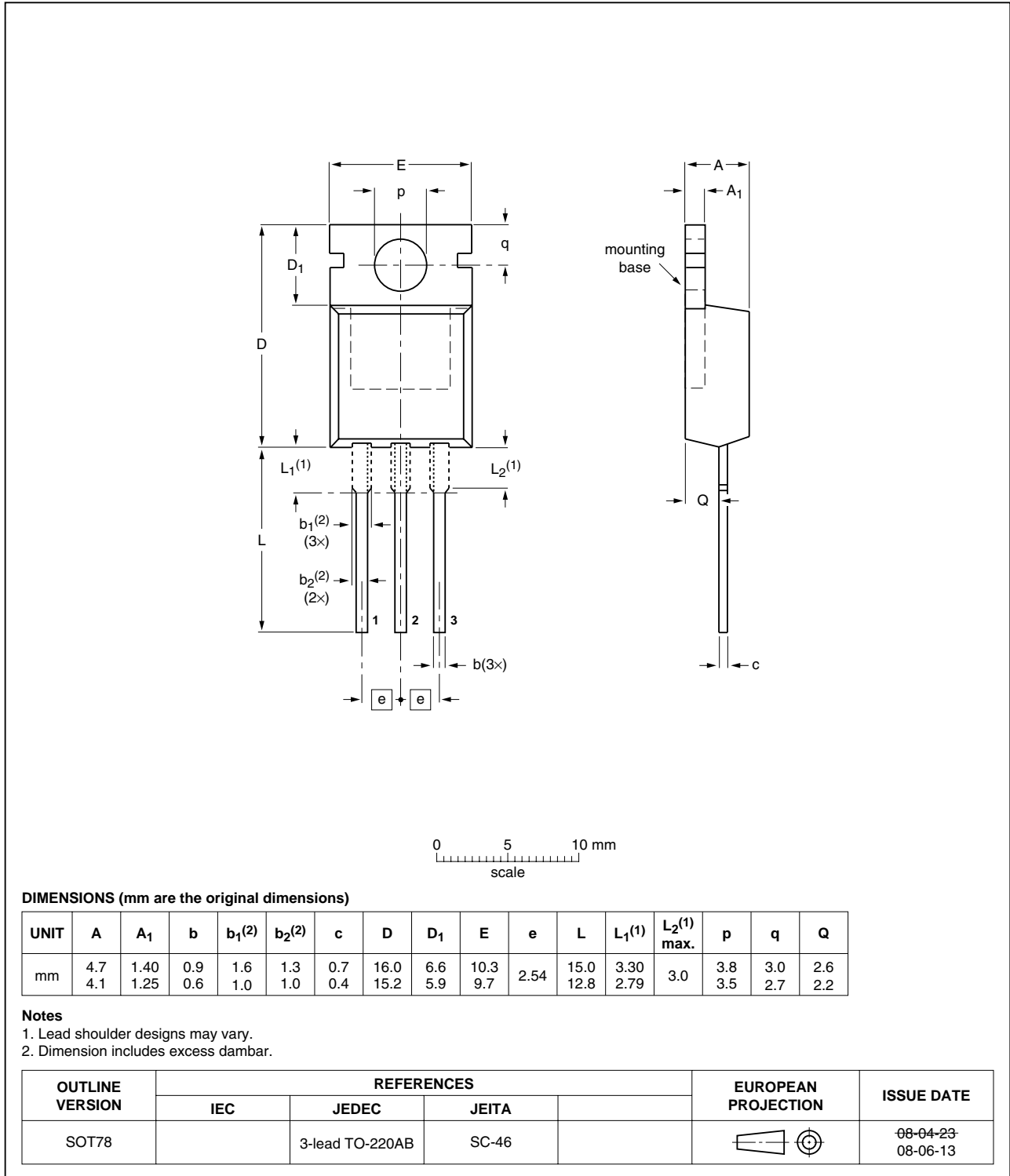


Fig 16. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHD13005 v.2	20100729	Product data sheet	-	PHD13005 v.1
Modifications:	• Various changes to content.			
PHD13005 v.1	20100520	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	5
6	Characteristics	6
7	Package outline	10
8	Revision history	11
9	Legal information	12
9.1	Data sheet status	12
9.2	Definitions	12
9.3	Disclaimers	12
9.4	Trademarks	13
10	Contact information	13

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